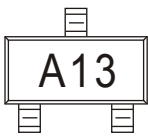


Plastic-Encapsulate Diodes

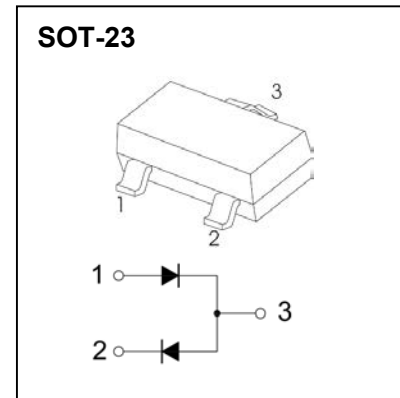
FEATURES

- Low Leakage
- High Conductance

MARKING: A13



Solid dot = Green molding compound device, if none, the normal device.



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_R	DC Blocking Voltage	200	V
I_o	Continuous Forward Current	200	mA
I_{FM}	Peak Forward Current	700	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	2.0	A
P_D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	357	$^\circ\text{C/W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=5\mu\text{A}$	200			V
Reverse current	I_R	$V_R=180\text{V}$			10	nA
Forward voltage	V_F	$I_F=1\text{mA}$			0.75	V
		$I_F=10\text{mA}$			0.85	
		$I_F=50\text{mA}$			0.95	
		$I_F=100\text{mA}$			1.1	
		$I_F=200\text{mA}$			1.3	
		$I_F=300\text{mA}$			1.5	
Total capacitance	C_{tot}	$V_R=0\text{V}, f=1\text{MHz}$			4	pF

Typical Characteristics

